

IN THE SPECIFICATION

Please amend the specification as indicated below.

[040] Next, as best depicted in Figure 12, body contact region 35 is created in an upper region of substrate 12 and therefore in an upper region of implant region 32. In one aspect of the invention, the body contact region 35 can be created using any suitable doping process that will obtain the desired profile and concentration. For example, the body contact region can be created by implanting B, P, or As at about 40-100KeV with a dose of about 1×10^{14} to about 8×10^{15} . Then, the dopant is driven into the substrate by a standard furnace anneal or a rapid thermal anneal.